Supporting Information

Fabrication and improved photoelectrochemical properties of transferred GaN-based thin film with InGaN/GaN layers

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Fig. S1 The only etched InGaN/GaN layer of GaN-based film for (a) cross-sectional SEM image and (b) photoconversion efficiency.

Fig. S2 Photoconversion efficiency as a function of applied potential of the plane n-Si.

Fig. S3 The XPS overview spectrum of the etched sample before and after PEC water splitting at 0.15 V for 4h.

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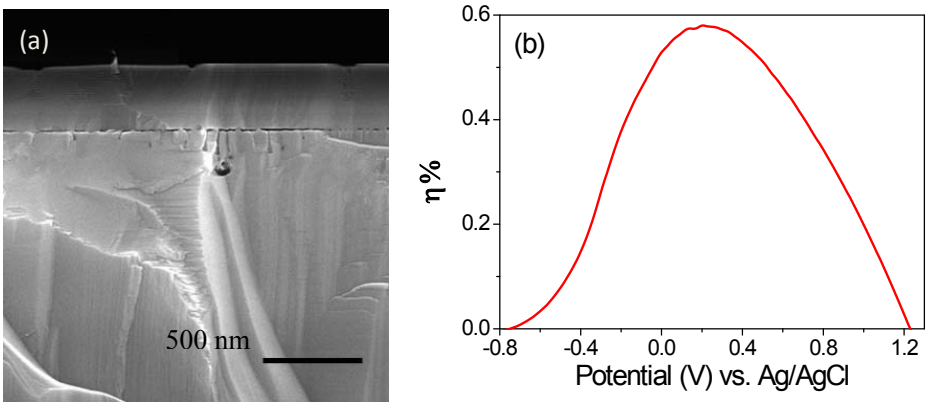

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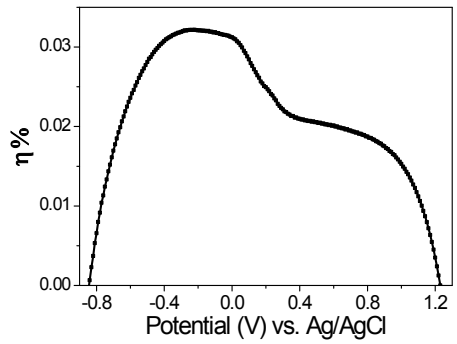
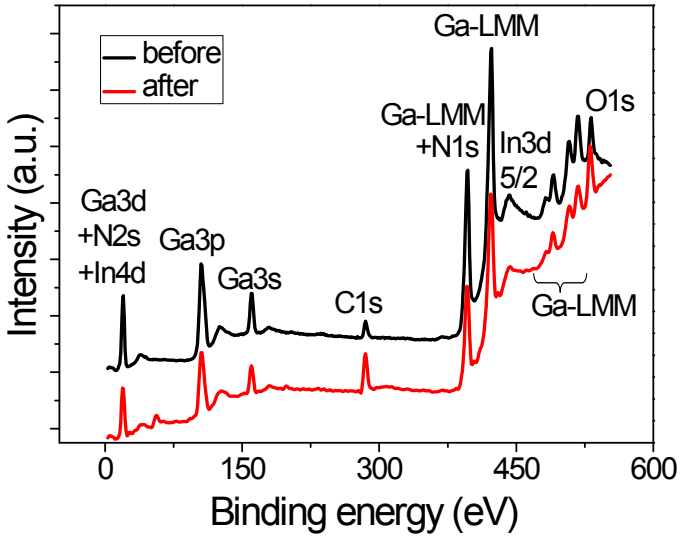


Fig. S2 Photoconversion efficiency as a function of applied potential of the plane n-Si.



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